

500V N-Channel Depletion-Mode Power MOSFET

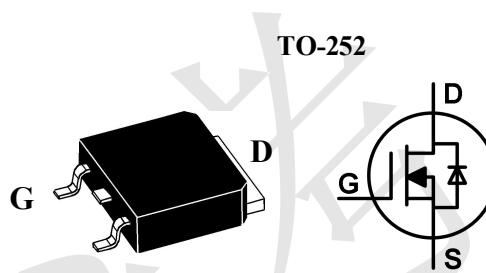
General Features

- Depletion Mode (Normally On)
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free Available
- Low $R_{DS(on)}$ Process
- International Standard Packages

BV_{DSX}	$R_{DS(ON)} (Max.)$	$I_{DSS(Min)}$
500V	30Ω	0.2A

Applications

- Suppressing Surge Current
- Start-up Circuits
- Converters
- Synchronous Rectification
- Constant Current Source
- Protection Circuits
- Level Shifting
- Triggers
- Solid State Relays
- Current Regulators



Ordering Information

Part Number	Package	Marking	Remark
DMD22C50A	TO-252	22C50A	Halogen Free

Absolute Maximum Ratings

$T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	DMD22C50A	Unit
V_{DSX}	Drain-to-Source Voltage	500	V
V_{DGX}	Drain-to-Gate Voltage	500	V
P_D	Power Dissipation	25	W
	Derating Factor above 25°C	25	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
T_L	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.